AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS

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(Currently Amended) High-speed In a method of depositing diamond films from the a gaseous phase in the a plasma of a microwave discharge, when the microwave discharge is formed in the a gaseous mixture placed in the <u>a</u> reaction chamber and consisting of <u>comprising</u> at least hydrogen and hydrocarbon, wherein the said gaseous mixture is activated by means of a microwave discharge to form atoms of hydrogen and carbon-containing radicals, and the form are deposited on the substrate and polycrystalline diamond film as the result of surface reactions, which differs in that the improvement which comprises:

activating the said gaseous mixture is activated by means of increasing so as to increase a density of electrons, Ne, in the plasma by means of creating a stable, non-equilibrium plasma with its a power at least 1 kW and frequency f that exceeds by far the a frequency of 2.45 GHz, which is used commonly, in the reaction chamber, and, in order to localize the plasma, as a standing wave

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microwave with nodes near the substrate is formed and at

its nodes plasma layers with the possibility to control

their dimensions as a layer over the substrate which plasma

is are generated and maintained by microwave beams directed

at and converging on the standing microwave so as to

deposit diamond film on the substrate.

- 2. (Currently Amended) High-speed The method as described 1 in par. 1, of Claim 1 which differs in that the wherein 2 said gaseous mixture is activated by means of increasing 3 electron density Ne by using electromagnetic radiation with 4 its frequency f equal to 30 GHz, and the dimensions of the 5 6 plasma layers in the nodes of the standing microwave are 7 controlled by changing the profiles and size of the a transverse cross-section of the crossing wave beams that form the standing wave. 9
- 3. (Currently Amended) High-speed The method as described in par. 1 or par. 2, of Claim 1 or 2 wherein which differs in that four or more of the wave beams that are crossed pairwise are used to form the standing wave.

- 4. (Currently Amended) High-speed The method as described
- 2 in par. 1 or par 2, of Claim 1 or 2 wherein which differs
- 3 in that two converging crossing wave beams are used to form
- 4 the standing wave.
- 5. (Currently Amended) High-speed The method as described
- 2 in par. 1 or par. 2, of Claim 1 or 2 wherein which differs
- 3 in that two converging opposite wave beams are used to form
- 4 the standing wave.
- 6. (Currently Amended) High-speed The method as described
- 2 in par. 1 or par. 2, of Claim 1 or 2 wherein which differs
- 3 in that the wave beam is incident on the substrate and the
- 4 wave beam is reflected from the substrate are used to form
- 5 the standing wave.
- 1 7. (Currently Amended) Plasma A reactor system for high-
- 2 speed deposition of diamond films from the a gaseous phase
- 3 in the <u>a</u> plasma of a microwave discharge, which <u>system</u>
- 4 contains a microwave generator, a transmission line ending
- 5 with a quasi-optical electrodynamic system, a reaction
- 6 chamber with a substrate on a substrate holder placed in it
- 7 the chamber, and a system for pump-in and pump-out of the
- 8 selected gaseous mixture, which differs in that the the

IOAP 4.1-1
Preliminary to First Office Action
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- 9 improvement which comprises a quasi-optical electrodynamic 10 system is made and installed such as to make it possible to 11 adapted to form a standing microwave in the an area 12 selected in the a vicinity of the substrate, and the 13 transmission line is made as an oversized circular waveguide with corrugation of its internal surface, which 14 15 is supplemented with a mirror system to transfer at least one Gaussian beam to the said quasi-optical electrodynamic 16 17 system.
- 1 8. (Currently Amended) Plasma The reactor as described in par. 7, system of Claim 7 which differs in that wherein the 2 3 quasi-optical system is made of has four mirrors situated on different sides relative to the a region of plasma 5 formation and installed in order to make it possible to direct the microwave radiation as four wave beams, wherein 6 7 the crossing is pairwise, and wherein the quasi-electrodynamic system together with a part of the 8 9 transmission line are installed within the chamber, and wherein the transmission line is supplemented 10 with a divider, which divides one wave beam into four beams 11 12 and is installed at the an output of the said oversized circular waveguide. 13

1 9. (Currently Amended) Plasma The reactor as described in par. 7, system of Claim 7 wherein which differs in that the 2 3 quasi-optical system is made of two mirrors situated on different sides relative to the a region of plasma 5 formation and installed in order to make it possible positioned so as to direct the two beams of the microwave 6 7 radiation at small angles to the a substrate surface of the substrate, and the transmission line is supplemented with 8 a divider, which divides one wave beam into two beams and 9 10 is installed at the <u>an</u> output of the said oversized circular waveguide. 11

- 1 10. (Currently Amended) Plasma The reactor system as 2 described in par. 7, of Claim 7 wherein which differs in 3 that the quasi-optical system is made of two mirrors situated on different sides relative to the a region of 5 plasma formation and installed in order to make it possible positioned so as to direct the wave beams opposite to each 6 7 other, and wherein one of the two mirrors is installed so as to be movable forward and backward parallel to itself to 8 9 the a distance of $\pm \lambda/4$, where λ is microwave radiation the transmission line 10 wavelength, and wherein is 11 supplemented with a divider, which divides one wave beam into two beams and is installed at the an output of the 12 13 said oversized circular wavequide.
- 1 11. (Currently Amended) Plasma The reactor system as described in par. 7, of Claim 7 wherein which differs in 2 that the \underline{a} bottom part of the reaction chamber has a 3 dielectric window to inject microwave radiation, and the 5 substrate is installed in the a top part of the chamber 6 opposite to the window, and wherein the quasi-optical electrodynamic system is made as one mirror situated out of 7 and lower than the said reaction chamber so as to make it 8 possible 9 to direct the <u>a</u> microwave beam upwards perpendicular to the substrate surface. 10

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- (Currently Amended) Plasma The reactor system as 1 12. described in par. 7, of Claim 7 wherein which differs in 2 that the quasi-optical electrodynamic system is made as has 3. one mirror installed so as to make it possible to direct the a microwave beam with normal incidence to the a 5 substrate surface of the substrate or at a low angle to the normal, and a cooled radioparent wall is installed in the 7 8 reaction chamber, which wall is made as a grating of thin cooled metal tubes or rods and is installed parallel to the 9 10 surface of the substrate at the <u>a</u> distance longer than $\lambda/2$ 11 from the- substrate.
 - 13. (Currently Amended) Plasma The reactor system as described in par. 7, of Claim 7 wherein which differs in that the quasi-optical electrodynamic system is made has as a mirror and a quasi-optical resonator with plane-parallel mirrors set at the a distance multiple of $\lambda/2$, which resonator is coupled with the electrodynamic system, and wherein one of the resonator mirrors is a surface of the substrate on the substrate holder, and the other mirror is made as comprises a periodic grating of thin metal tubes or rods, wherein a and the grid period of the grid is less than λ .

- 1 (Currently Amended) Plasma The reactor system as 2 described in par. 8 or par 9, or par. 10, of any one of Claims 8, 9 or 10 wherein which differs in that the a 3 system for pumping gas into the reaction chamber into the region of the plasma formation is made as a concave metal 5 6 screen with a feeding tube in its a central part, and this the screen is situated over the substrate holder at an 7 8 adjustable distance, and the system for pumping the gas out 9 is made as a set of apertures in the substrate support, 10 which has some a volume for the evacuated gas mixture, and 11 in this volume the system for water cooling of the upper 12 part of the substrate support is situated.
- 1 (Currently Amended) Plasma The reactor system as 2 described in part. 12 or par. 13, of Claim 12 or 13 wherein 3 which differs in that the a system for pumping the selected gas mixture in is combined with the grating made of which is thin cooled metal tubes, and wherein the system for 5 pumping the gas out is made as a set of apertures in the 6 7 substrate holder, which has some volume a portion for the 8 evacuated gas mixture, and in this volume the system a 9 portion for water cooling of the an upper part of the 10 substrate holder is situated.